

one pixel cell comprising: a semiconductor substrate including a strained silicon layer at an upper portion thereof; and a photosensor for generating charge formed in an upper region of said semiconductor substrate..” Dependent claim 8 recites the pixel cell of claim 1 “further comprising a reset transistor, a source follower transistor, and a row select transistor formed in regions of said substrate containing said strained layer.” Dependent claim 9 recites the pixel cell of claim 8 “further comprising a transfer transistor formed in a region of said substrate containing said strained silicon layer.” Applicant respectfully submits that claims 1-9 should be examined together because claim 1 is generic to claims 8 and 9 (i.e., Species II and III, respectively). Should the Examiner maintain that claim 1 is not generic to claims 8 and 9, however, Applicant respectfully submits that claims 1-9 can be examined together “without serious burden.”

Independent claim 39 recites “a method of forming a pixel cell comprising: forming a semiconductor substrate; forming a strained silicon layer in association with an upper portion of said semiconductor substrate; and forming a photosensor for generating charge at said upper portion of said semiconductor substrate.” Dependent claim 40 recites the method according to claim 39, “further comprising forming a reset transistor, a source follower transistor, and a row select transistor in regions of said substrate containing said strained layer.” Dependent claim 41 recites the method according to claim 40, “further comprising forming a transfer transistor in a region of said substrate containing said strained silicon layer.” Applicant respectfully submits that claims 39-48 should be examined together because claim 39 is generic to claims 40 and 41 (i.e., Species II and III, respectively). Should the Examiner maintain that claim 39 is not generic to claims 40 and 41, however, Applicant respectfully submits that claims 39-48 can be examined together “without serious burden.”

Independent claim 10 recites “at least one pixel cell comprising: a semiconductor substrate including a strained silicon layer at an upper portion; a photosensor for generating charge formed in an upper region of said semiconductor substrate; a reset transistor formed in association with said upper portion of said semiconductor substrate; a source follower transistor formed in association with said upper portion of said semiconductor substrate; and a row select transistor formed in association with said upper portion of said semiconductor substrate.” Applicant respectfully submits that claim 10 (and its dependent claims 11-16) can be examined together with claims 1-9 “without serious burden.”

Similarly, independent claim 17 recites “at least one pixel cell comprising: a semiconductor substrate including a strained silicon layer at an upper portion; a photosensor for generating charge formed in an upper region of said semiconductor substrate; a reset transistor formed in association with said upper portion of said semiconductor substrate; a source follower transistor formed in association with said upper portion of said semiconductor substrate; a row select transistor formed in association with said upper portion of said semiconductor substrate; and a transfer transistor formed in association with said upper portion of said semiconductor substrate.” Applicant respectfully submits that claim 17 (and its dependent claims 18-23) can be examined together with claims 1-16 “without serious burden.”

Applicant respectfully requests that claims 1-48 be examined in one application; however, should the Examiner maintain the election, Applicant respectfully submits that at least claims 1-23 and 39-48 can be examined together in one application “without serious burden.”

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Respectfully submitted,

By 

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